METHOD FOR TREATING A SUBSTRATE HAVING A SURFACE MADE OF A SEMICONDUCTOR MATERIAL

ABSTRACT

The present invention relates to a process for treating a substrate having a free surface made of a semiconductor material, notably a single-crystal semiconductor material, comprising a process for stabilizing said surface against the formation of terraces and/or beads, said process involving

- the formation in the gaseous phase, on said surface, of a layer of vitreous carbon (30) at a temperature (T1) above 700°C, preferably above 800°C, and strictly below 1000°C, preferably below 950°, and more preferably below 900°C, and
- a heat treatment of said substrate after stabilizing said surface, in which the vitreous carbon layer (30) limits the reorganization of the surface into a semiconductor material in the form of terraces,

the deposition of the carbon layer (30) and the heat treatment being performed in the same furnace.

Fig. 3